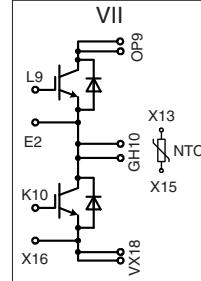


IGBT Modules in ECO-PAC 2

Short Circuit SOA Capability
Square RBSOA

I_{C25} = 121 A
 V_{CES} = 600 V
 $V_{CE(sat)\ typ.}$ = 2.3 V

Preliminary data sheet



Pin arrangement see outlines

IGBTs

Symbol	Conditions	Maximum Ratings		
V_{CES}	$T_{VJ} = 25^\circ\text{C}$ to 150°C	600	V	
V_{GES}		± 20	V	
I_{C25}	$T_C = 25^\circ\text{C}$	121	A	
I_{C80}	$T_C = 80^\circ\text{C}$	83	A	
I_{CM}	$V_{GE} = \pm 15 \text{ V}$; $R_G = 2.2 \Omega$; $T_{VJ} = 125^\circ\text{C}$	200	A	
V_{CEK}	RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$	360	V	
t_{sc} (SCSOA)	$V_{CE} = V_{CES}$; $V_{GE} = \pm 15 \text{ V}$; $R_G = 2.2 \Omega$; $T_{VJ} = 125^\circ\text{C}$ non-repetitive	10	μs	
P_{tot}	$T_C = 25^\circ\text{C}$	379	W	

Symbol	Conditions	Characteristic Values		
		($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)		
$V_{CE(sat)}$	$I_C = 130 \text{ A}$; $V_{GE} = 15 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.3 2.6	2.9 V	V
$V_{GE(th)}$	$I_C = 1.5 \text{ mA}$; $V_{GE} = V_{CE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}$; $V_{GE} = 0 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		1.2 7.5	mA mA
I_{GES}	$V_{CE} = 0 \text{ V}$; $V_{GE} = \pm 20 \text{ V}$		400	nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^\circ\text{C}$ $V_{CE} = 300 \text{ V}$; $I_C = 80 \text{ A}$ $V_{GE} = 15/0 \text{ V}$; $R_G = 2.2 \Omega$	25 11 150 30 0.8 2.3		ns ns ns ns mJ mJ
C_{ies}	$V_{CE} = 25 \text{ V}$; $V_{GE} = 0 \text{ V}$; $f = 1 \text{ MHz}$	4.2		nF
R_{thJC} R_{thJH}	(per IGBT) with heatsink compound (0.42 K/m.K; 50 μm)		0.33 0.66	K/W K/W

IXYS reserves the right to change limits, test conditions and dimensions.

© 2006 IXYS All rights reserved

Reverse diodes (FRED)

Symbol	Conditions	Maximum Ratings		
I _{F25}	T _C = 25°C	134.0	A	
I _{F80}	T _C = 80°C	82.3	A	

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V _F	I _F = 80 A; T _{VJ} = 25°C T _{VJ} = 125°C	1.85 1.40	2.06	V V
I _{RM} t _{rr}	I _F = 60 A; dI/dt = 500 A/μs; T _{VJ} = 125°C V _R = 300 V; V _{GE} = 0 V	28 100		A ns
R _{thJC} R _{thJH}	with heatsink compound (0.42 K/m.K; 50 μm)	1.32	0.66 K/W K/W	

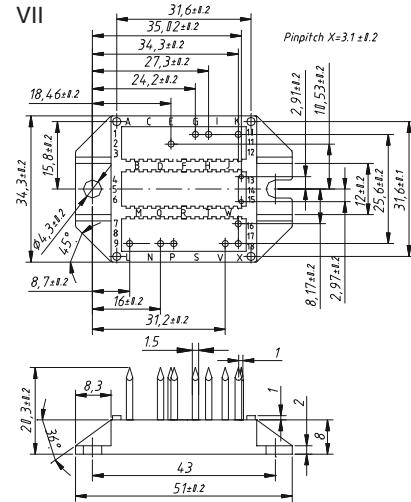
Temperature Sensor NTC

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R ₂₅	T = 25°C	4.75	5.0	5.25 kΩ
B _{25/50}			3375	K

Module

Symbol	Conditions	Maximum Ratings		
T _{VJ}		-40...+150	°C	
T _{stg}		-40...+150	°C	
V _{ISOL}	I _{ISOL} ≤ 1 mA; 50/60 Hz	3000	V~	
M _d	mounting torque (M4)	1.5 - 2.0 14 - 18	Nm lb.in.	
a	Max. allowable acceleration	50	m/s ²	

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d _s	Creepage distance on surface (Pin to heatsink)	11.2		mm
d _A	Strike distance in air (Pin to heatsink)	11.2		mm
Weight		24		g



Data according to IEC 60747 and refer to a single transistor or diode unless otherwise stated.
IXYS reserves the right to change limits, test conditions and dimensions.